



General Description

The QM3002N3 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The QM3002N3 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	28		A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	18		A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	11.7	7.4	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	9.4	6	A
I_{DM}	Pulsed Drain Current ²	56		A
EAS	Single Pulse Avalanche Energy ³	72		mJ
I_{AS}	Avalanche Current	21		A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	20.8		W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	4.2	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150		$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150		$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	75	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	---	30	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	6	$^\circ C/W$

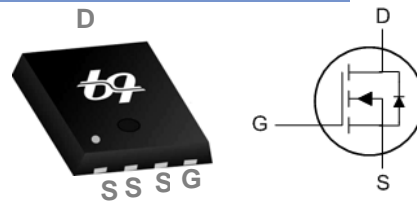
Product Summary

BVDSS	RDSON	ID
30V	18m Ω	28A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3X3 Pin Configuration



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.022	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=15A$	---	16	18	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	24	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.1	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5V, I_D=30A$	---	19.4	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.5	5	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=15A$	---	6.2	8.7	nC
Q_{gs}	Gate-Source Charge		---	2.4	3.4	
Q_{gd}	Gate-Drain Charge		---	2.5	3.5	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=10V, V_{GS}=10V, R_G=3.3\Omega, I_D=15A$	---	3	6.0	ns
T_r	Rise Time		---	7.6	14	
$T_{d(off)}$	Turn-Off Delay Time		---	20.8	42	
T_f	Fall Time		---	4	8	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	572	801	pF
C_{oss}	Output Capacitance		---	80	112	
C_{riss}	Reverse Transfer Capacitance		---	65	91	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	$V_{DD}=25V, L=0.1\text{mH}, I_{AS}=10A$	16	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	28	A
I_{SM}	Pulsed Source Current ^{2,6}		---	---	56	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=30A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	17	---	nS
Q_{rr}	Reverse Recovery Charge		---	3	---	nC

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The EAS data shows Max. rating. The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=21A$
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

N-Ch 30V Fast Switching MOSFETs

Typical Characteristics

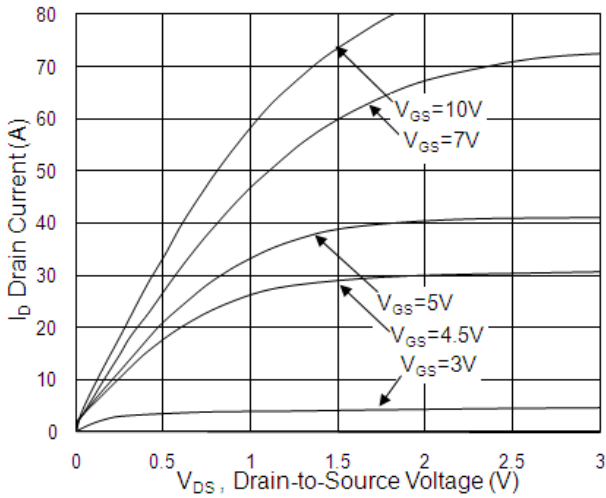


Fig.1 Typical Output Characteristics

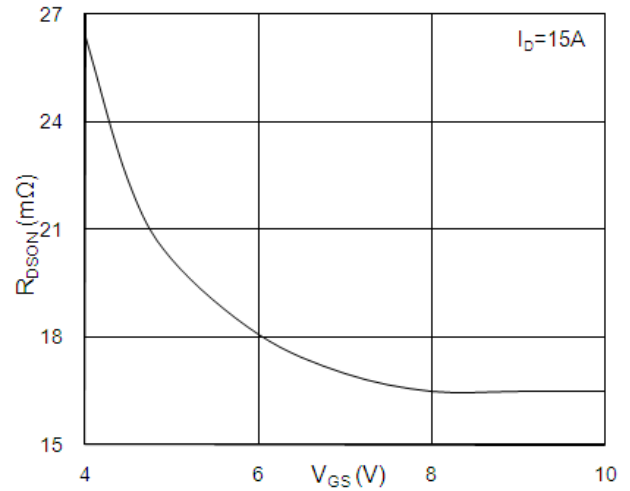


Fig.2 On-Resistance vs. Gate-Source

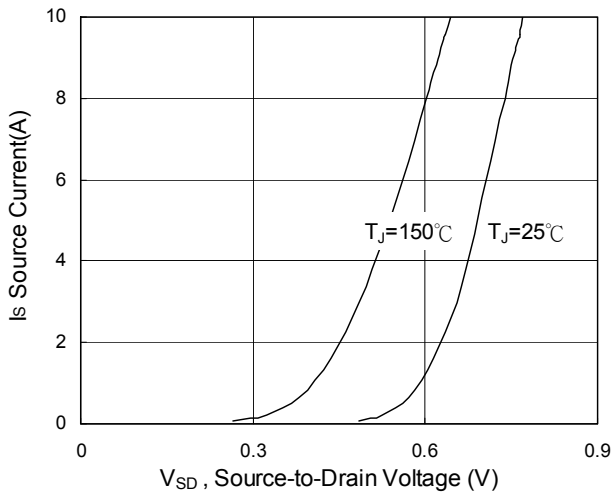


Fig.3 Forward Characteristics Of Reverse

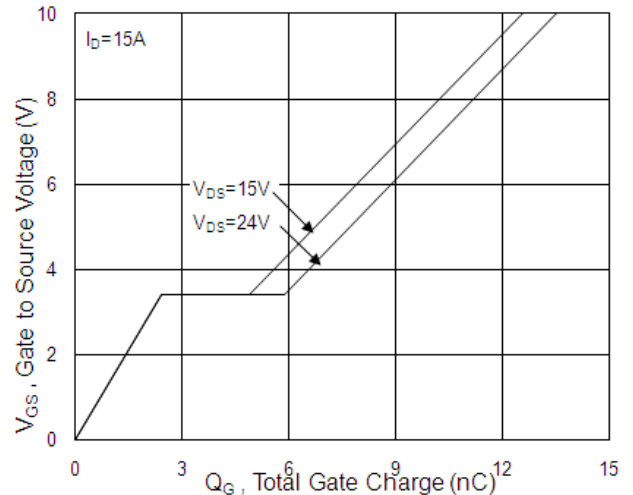


Fig.4 Gate-Charge Characteristics

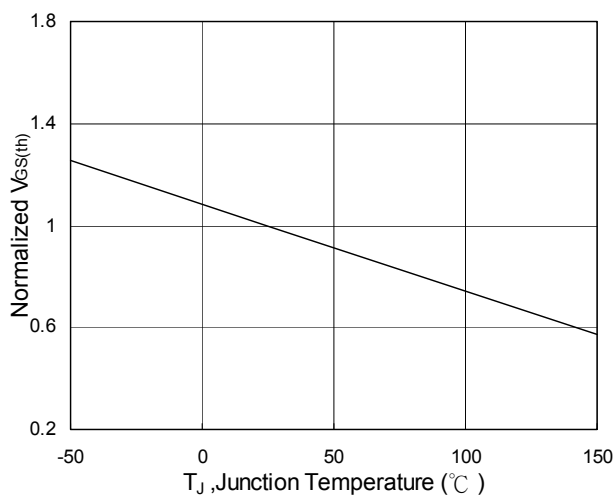


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

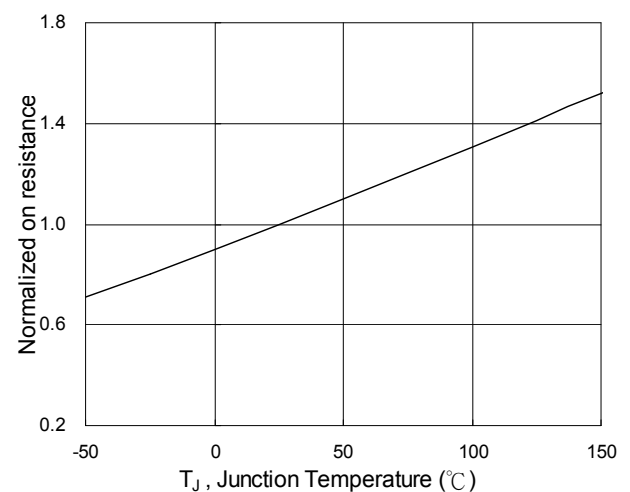


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

N-Ch 30V Fast Switching MOSFETs

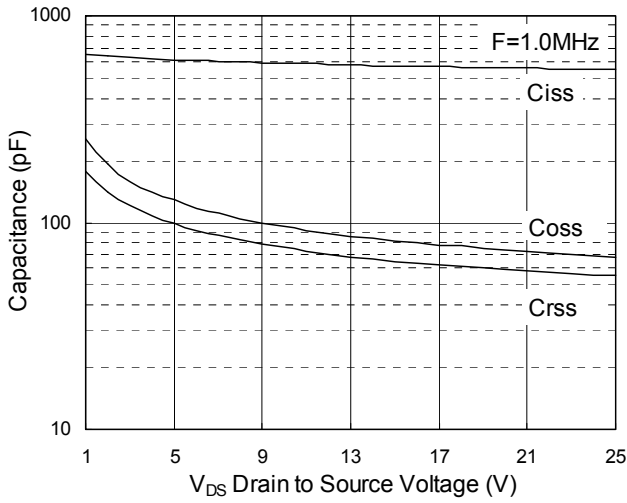


Fig.7 Capacitance

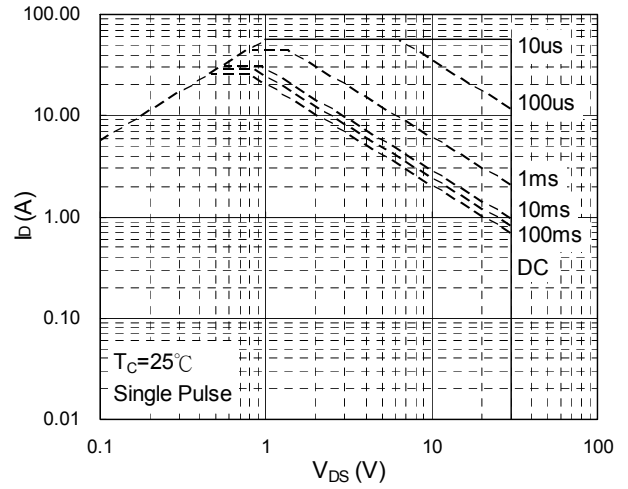


Fig.8 Safe Operating Area

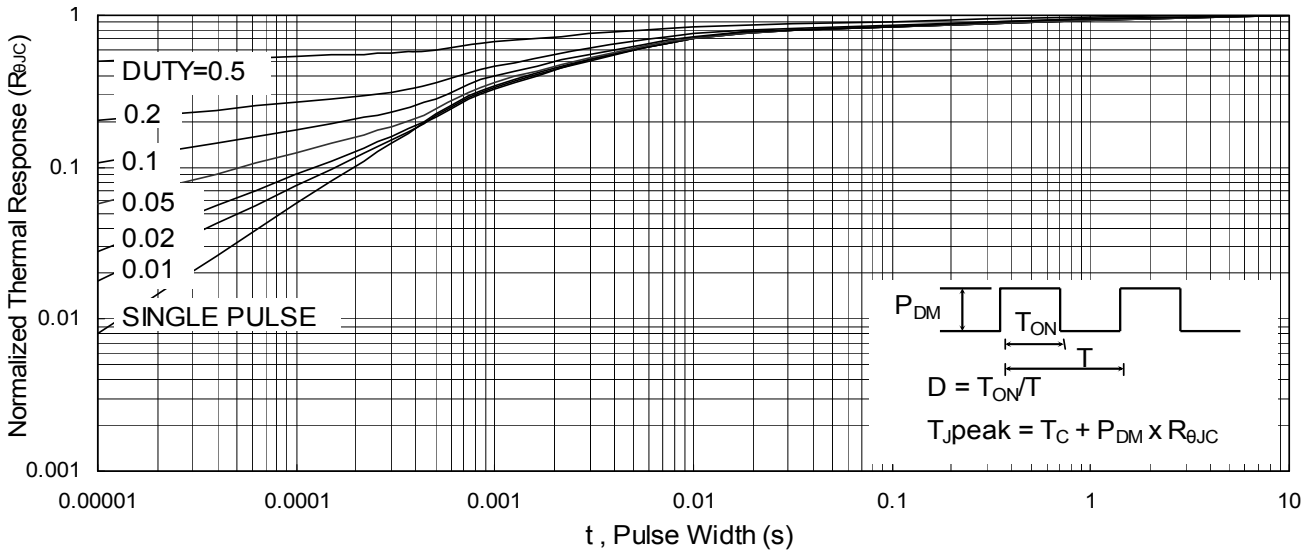


Fig.9 Normalized Maximum Transient Thermal Impedance

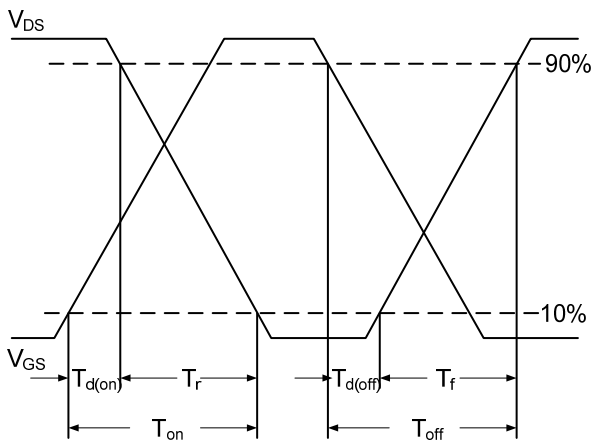


Fig.10 Switching Time Waveform

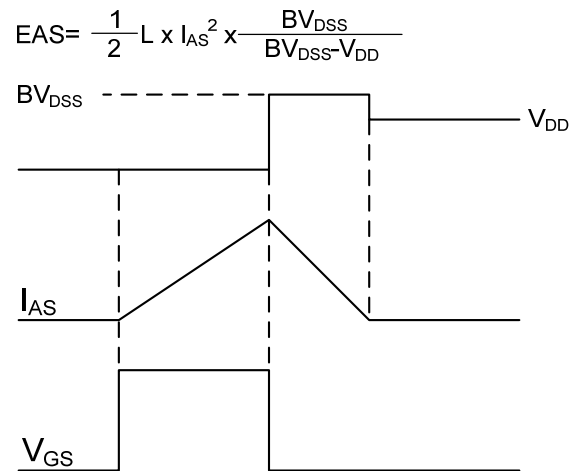


Fig.11 Unclamped Inductive Switching Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$